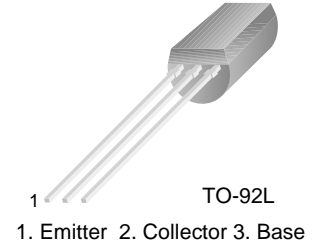


**■■ APPLICATION:** High Voltage Applications.

**■■ MAXIMUM RATINGS** ( $T_a=25^\circ\text{C}$ )

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	$V_{CBO}$	-120	V
Collector-emitter voltage	$V_{CEO}$	-120	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-800	mA
Collector Power Dissipation	$P_C$	1	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ\text{C}$


**■■ ELECTRICAL CHARACTERISTICS** ( $T_a=25^\circ\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	$h_{FE}$	80		240		$V_{CE} = -5V, I_C = -100mA$
Collector Cut-off Current	$I_{CBO}$			-0.1	$\mu\text{A}$	$V_{CB} = -120V, I_E = 0$
Emitter Cut-off Current	$I_{EBO}$			-0.1	$\mu\text{A}$	$V_{EB} = -5V, I_C = 0$
Collector-Base Breakdown Voltage	$BV_{CBO}$	-120			V	$I_C = -1mA, I_E = 0$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	-120			V	$I_C = -10mA, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5			V	$I_E = -1mA, I_C = 0$
Base-Emitter Voltage	$V_{BE}$			-1	V	$V_{CE} = -5V, I_C = -500mA$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-1	V	$I_C = -500mA, I_B = -50mA$
Gain bandwidth product	$f_T$	50	120		MHz	$I_C = -100mA, V_{CE} = -5V$
Common Base Output Capacitance	$C_{ob}$			40	pF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

**■■  $h_{FE}$  Classification**

Classification	O	Y
$h_{FE}$	80~160	120~240